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ne<mark>x</mark>peria

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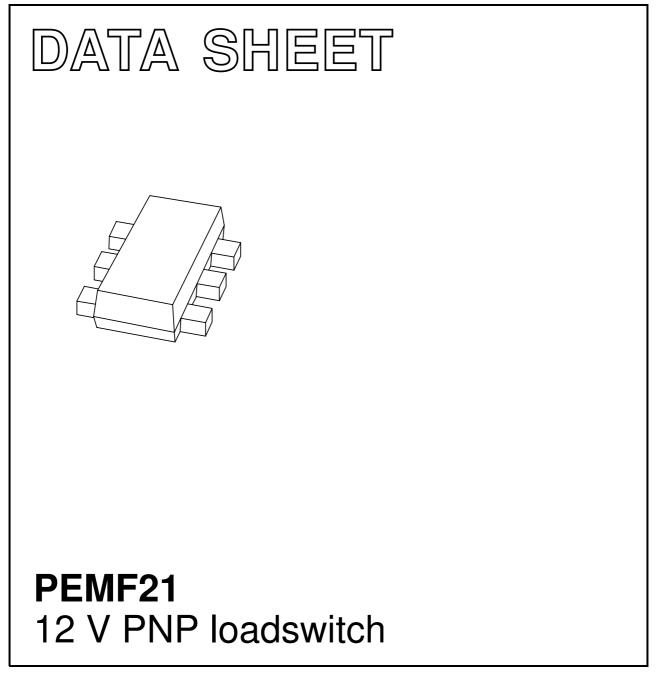
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DISCRETE SEMICONDUCTORS



Product data sheet

2004 Jan 12



FEATURES

- Low V_{CEsat} transistor and resistor-equipped transistor in one package
- Very small 1.6×1.2 mm ultra thin package
- Reduced component count.

APPLICATIONS

- Line switches
- Battery charger switches
- Power supply switches
- Drive switches
- General purpose analog switches.

DESCRIPTION

Low V_{CEsat} PNP transistor and NPN resistor-equipped transistor in a SOT666 plastic package (see "Ordering information" for package details).

MARKING

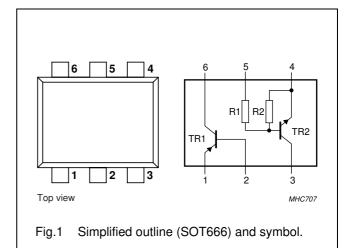
TYPE NUMBER	MARKING CODE
PEMF21	2F

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
TR1; PNP	; Iow V _{CEsat} transistor			
V _{CEO}	collector-emitter voltage	_	-12	V
I _C	collector current (DC)	-	-500	mA
R _{CEsat}	equivalent on-resistance	_	500	mΩ
TR2; NPN	; resistor-equipped tra	ansisto	r	
V _{CEO}	collector-emitter voltage	_	50	V
lo	output current (DC)	-	100	mA
R1	bias resistor	10	_	kΩ
R2	bias resistor	10	-	kΩ

PINNING

PIN	DESCRIPTION	
1	emitter TR1	
2	base TR1	
3	collector TR2	
4	emitter TR2	
5	base TR2	
6	collector TR1	



ORDERING INFORMATION

TYPE NUMBER		PACKAGE		
	NAME	DESCRIPTION	VERSION	
PEMF21	—	plastic surface mounted package; 6 leads		

PEMF21

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Transistor TR	1	·	·		
V _{CBO}	collector-base voltage	open emitter	_	-15	V
V _{CEO}	collector-emitter voltage	open base	-	-12	V
V _{EBO}	emitter-base voltage	open collector	_	-6	V
I _C	collector current (DC)		_	-500	mA
I _{CM}	peak collector current		_	-1	А
I _{BM}	peak base current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	200	mW
Transistor TR	2	· ·		<u>.</u>	•
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
Vi	input voltage				
	positive		_	+40	V
	negative		_	-10	V
lo	output current (DC)		_	100	mA
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	200	mW
Per device		·	·		
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	-	300	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per device				
R _{th(j-a)}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. Reflow soldering is the only recommended soldering method.

PEMF21

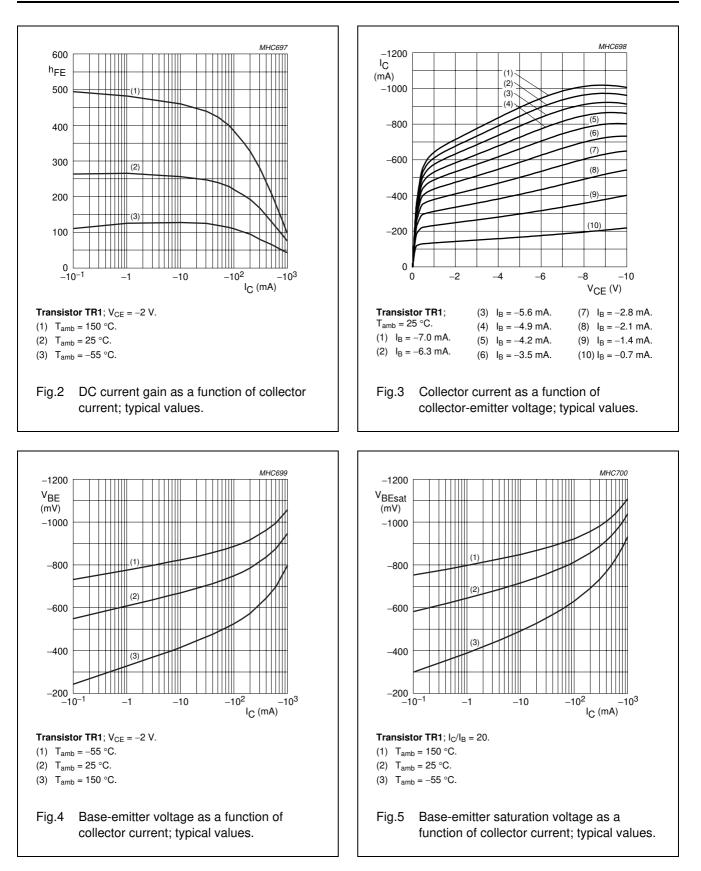
CHARACTERISTICS

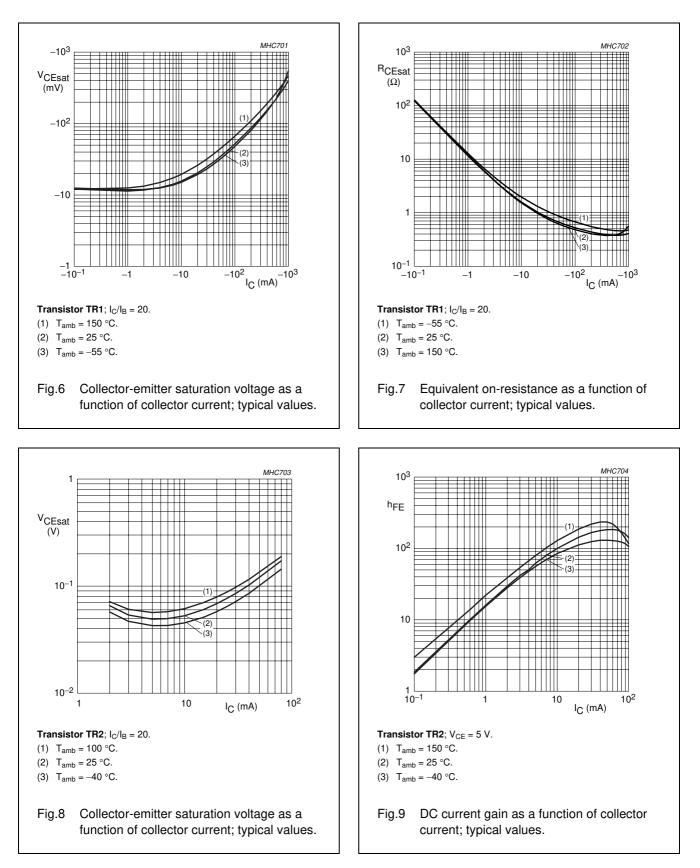
 T_{amb} = 25 °C unless otherwise specified.

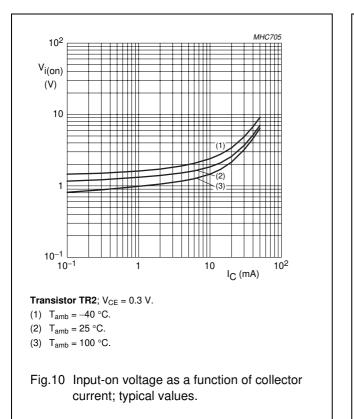
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Transistor TR1						
I _{CBO}	collector-base cut-off current	$V_{CB} = -15 \text{ V}; I_E = 0$	-	_	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -10 \text{ mA}$	200	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -200 \text{ mA}; I_{\rm B} = -10 \text{ mA}$	-	-	-250	mV
R _{CEsat}	equivalent on-resistance	$I_{C} = -500 \text{ mA}; I_{B} = -50 \text{ mA}; \text{ note } 1$	-	300	500	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_{C} = -500 \text{ mA}; I_{B} = -50 \text{ mA}; \text{ note } 1$	-	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -100 \text{ mA}; \text{ note } 1$	-	-	-0.9	V
f _T	transition frequency	$I_{C} = -100 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	280	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	-	-	10	pF
Transistor	TR2					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0$	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0$	-	_	1	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0$	-	-	400	μA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	30	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = 10 \text{ mA}; I_{\rm B} = 0.5 \text{ mA}$	-	_	300	mV
V _{i(off)}	input-off voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	-	0.5	V
V _{i(on)}	input-on voltage	V _{CE} = 0.3 V; I _C = 10 mA	3	_	_	V
R1	input resistor		7	10	13	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	V _{CB} = 10 V; I _E = i _e = 0; f = 1 MHz	_	_	2.5	pF

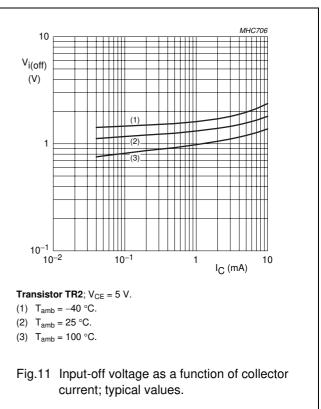
Note

1. Pulse test: $t_p \leq 300~\mu\text{s};~\delta \leq 0.02.$

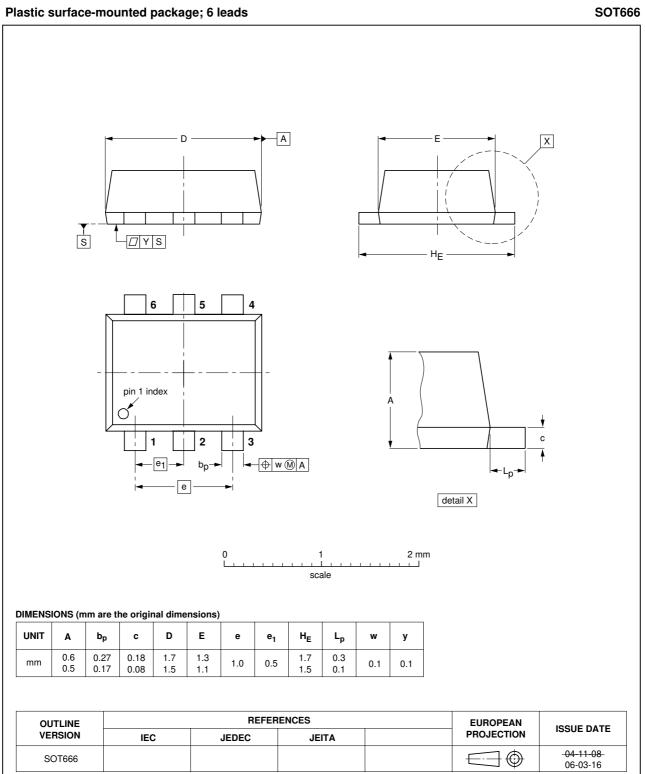








PACKAGE OUTLINE



PEMF21

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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